

THYRISTOR MODULE

PK(PD,PE,KK)90GB

TOP



UL;E76102 (M)

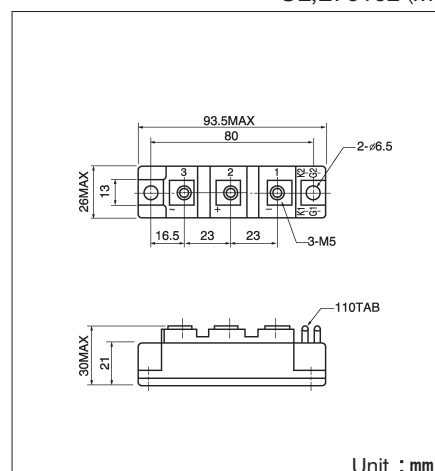
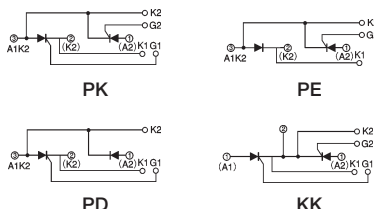
Power Thyristor/Diode Module **PK90GB** series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 800V are available, and electrically isolated mounting base make your mechanical design easy.

- $I_{T(AV)}$ 90A, $I_{T(RMS)}$ 140A, I_{TSM} 1800A
- di/dt 200 A/ μ s
- dv/dt 500V/ μ s

(Applications)

Various rectifiers
AC/DC motor drives
Heater controls
Light dimmers
Static switches

Internal Configurations



Maximum Ratings

Maximum Ratings

Symbol	Item	Ratings				Unit
		PK90HB120 KK90HB120	PD90HB120 PE90HB120	PK90HB160 KK90HB160	PD90HB160 PE90HB160	
V _{RRM}	* Repetitive Peak Reverse Voltage	400		800		V
V _{RSM}	* Non-Repetitive Peak Reverse Voltage	480		960		V
V _{DRM}	* Non-Repetitive Peak Reverse Voltage	400		800		V

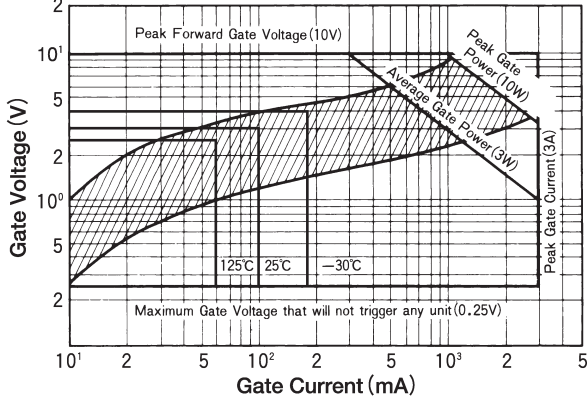
Symbol	Item	Conditions	Ratings	Unit	
I _{T (AV)}	* Average On-State Current	Single phase, half wave, 180° conduction, T _c : 88℃	90	A	
I _{T (RMS)}	* R.M.S. On-State Current	Single phase, half wave, 180° conduction, T _c : 88℃	140	A	
I _{TSM}	* Surge On-State Current	1½cycle, 50Hz/60Hz, peak Value, non-repetitive	1650/1800	A	
I ² t	* I ² t	Value for one cycle of surge current	15000	A²S	
P _{GM}	Peak Gate Power Dissipation		10	W	
P _{G (AV)}	Average Gate Power Dissipation		3	W	
I _{FGM}	Peak Gate Current		3	A	
V _{FGM}	Peak Gate Voltage (Forward)		10	V	
V _{RGM}	Peak Gate Voltage (Reverse)		5	V	
di/dt	Critical Rate of Rise of On-State Current	I _G = 100mA, T _j = 25℃, V _D = ½V _{DRM} , dI _G /dt = 0.1A/μs	200	A/μs	
V _{ISO}	* Isolation Breakdown Voltage (R.M.S.)	A.C. 1 minute	2500	V	
T _j	* Operating Junction Temperature		−40 ~ +125	℃	
T _{stg}	* Storage Temperature		−40 ~ +125	℃	
	Mounting Torque	Mounting (M6)	Recommended Value 2.5 ~ 3.9 (25 ~ 40)	4.7 (48)	N · m (kgf · cm)
		Terminal (M5)	Recommended Value 1.5 ~ 2.5 (15 ~ 25)	2.7 (28)	
	Mass		170	g	

Electrical Characteristics

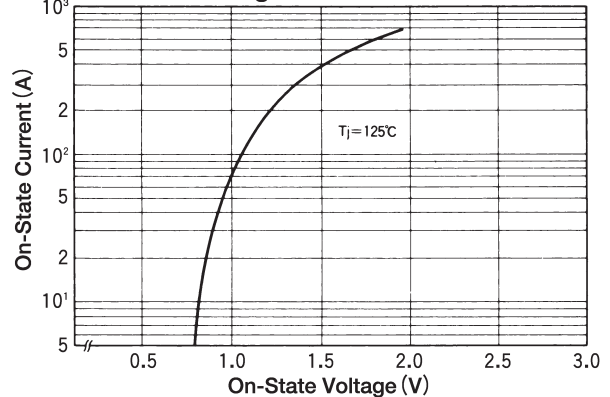
Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j = 125^\circ\text{C}$	15	mA
I_{RRM}	* Repetitive Peak Reverse Current, max.	at V_{DRM} , single phase, half wave, $T_j = 125^\circ\text{C}$	15	mA
V_{TM}	* Peak On-State Voltage, max.	On-State Current 270A, $T_j = 125^\circ\text{C}$ Inst. measurement	1.30	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.	$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	100/3	mA/V
V_{GD}	Non-Trigger Gate, Voltage. min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{1}{2}V_{DRM}$	0.25	V
t_{gt}	Turn On Time, max.	$I_T = 90\text{A}$, $I_G = 100\text{mA}$, $T_j = 25^\circ\text{C}$, $V_D = \frac{1}{2}V_{DRM}$, $dI_G/dt = 0.1\text{A}/\mu\text{s}$	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{2}{3}V_{DRM}$, Exponential wave.	500	V/ μs
I_H	Holding Current, typ.	$T_j = 25^\circ\text{C}$	50	mA
I_L	Latching Current, typ.	$T_j = 25^\circ\text{C}$	100	mA
$R_{th}(j-c)$	* Thermal Impedance, max.	Junction to case	0.30	°C/W

*mark : Thyristor and Diode part. No mark : Thyristor part

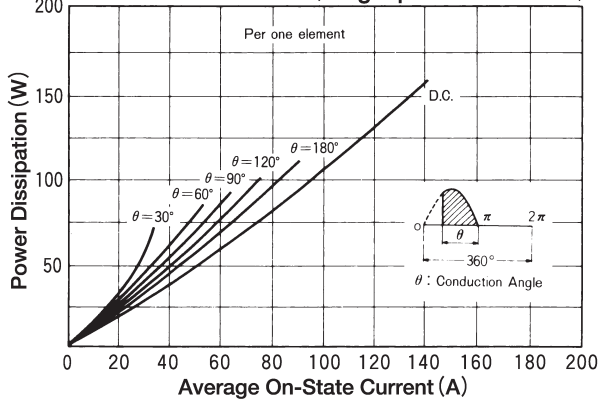
Gate Characteristics



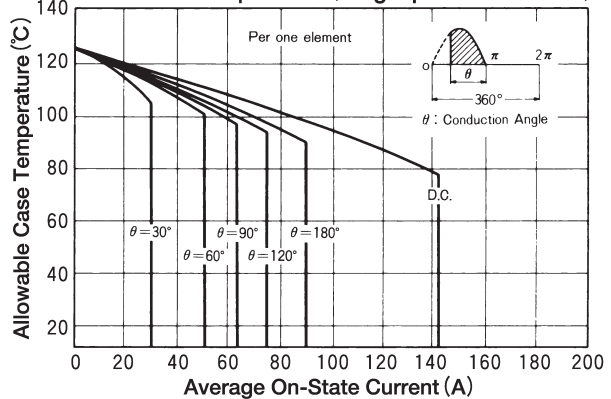
On-State Voltage max



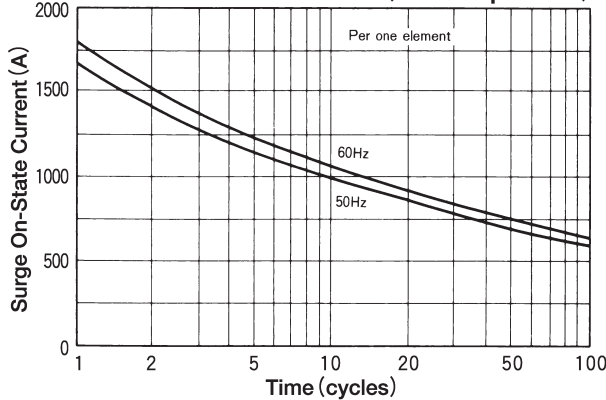
Average On-State Current Vs Power Dissipation (Single phase half wave)



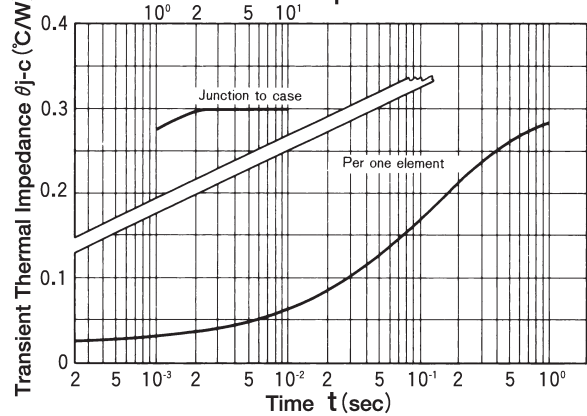
Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



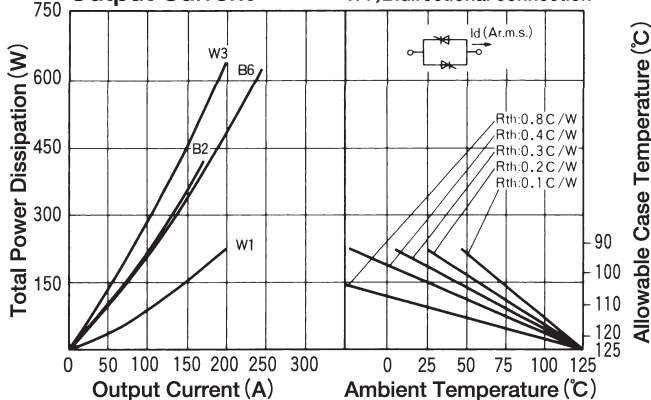
Surge On-State Current Rating (Non-Repetitive)



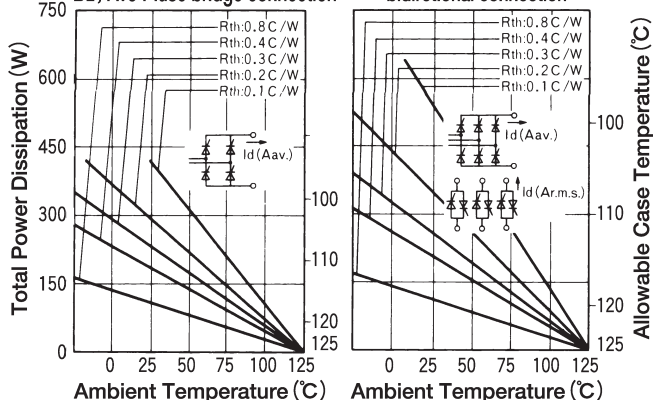
Transient Thermal Impedance



Output Current W1; Bidirectional connection



B2; Two Pulse bridge connection



B6; Six pulse bridge connection W3; Three phase bidirectional connection

